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Wilson et al.

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(54) **MULTI-DIRECTIONAL RADIATION COUPLING IN QUANTUM-WELL INFRARED PHOTODETECTORS**

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 17 days.

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(22) Filed: **Jun. 26, 2000**

Related U.S. Application Data

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(51) **Int. Cl.**⁷ **H01L 29/06**

(52) **U.S. Cl.** **257/21; 257/436; 257/460;**
438/32

(58) **Field of Search** 257/21, 436, 460;
250/338.4; 359/562, 563, 572, 575; 438/32

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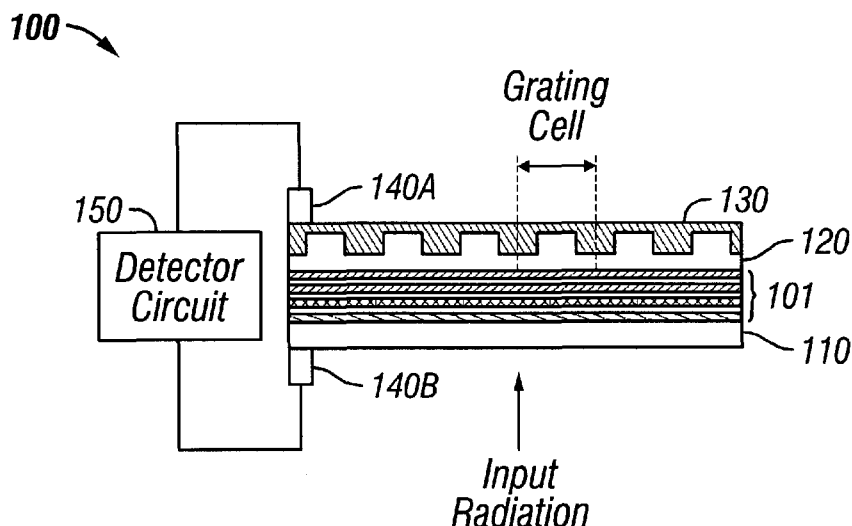
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(57) **ABSTRACT**

Techniques for coupling radiation into a quantum-well detector by using a two-dimensional array of grating cells to form at least three different grating directions to provide efficient coupling.

21 Claims, 2 Drawing Sheets



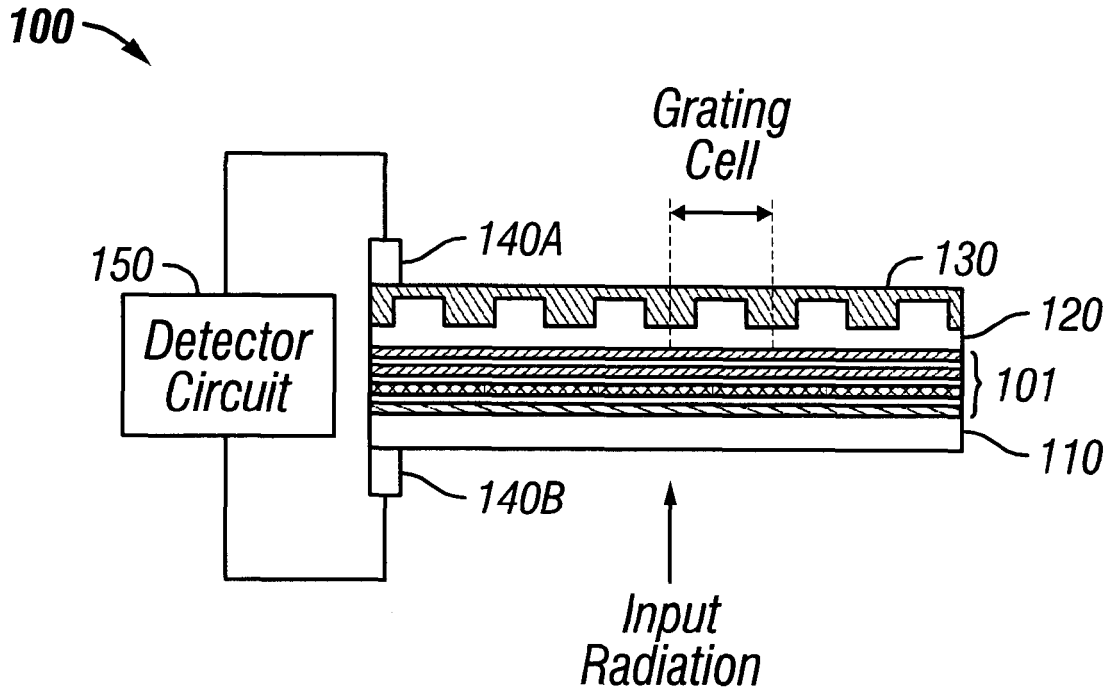


FIG. 1

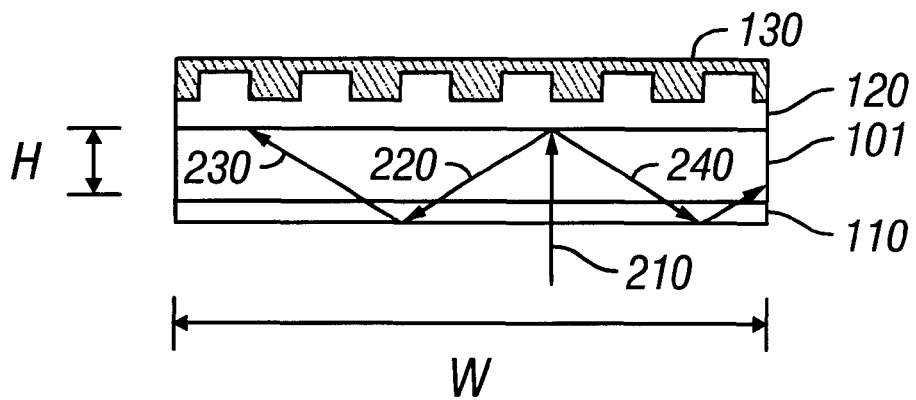


FIG. 2

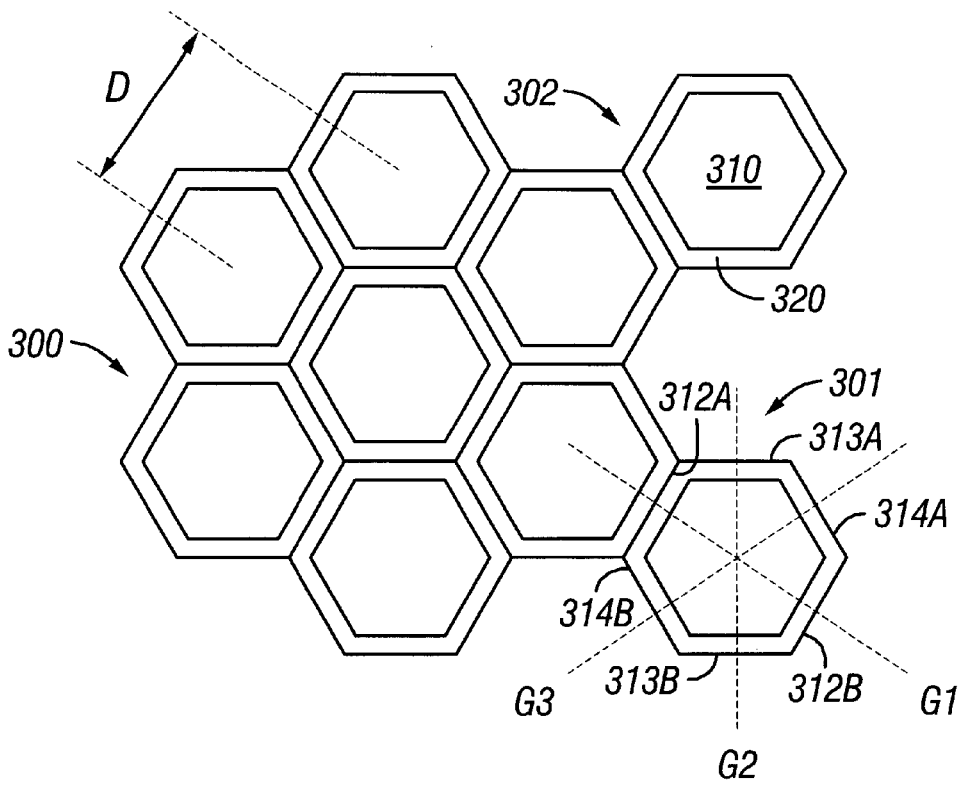


FIG. 3

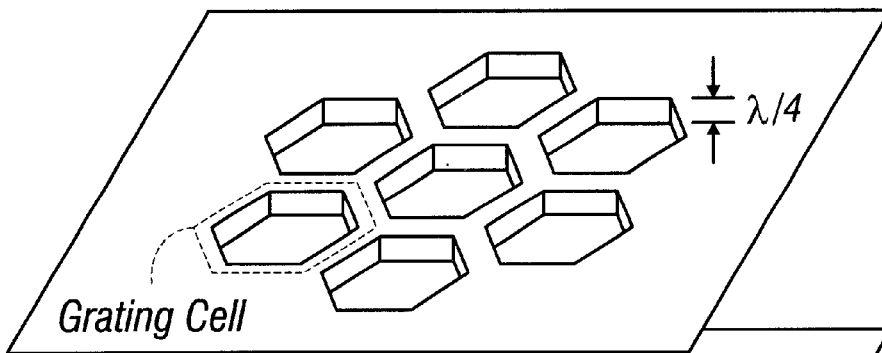


FIG. 4A

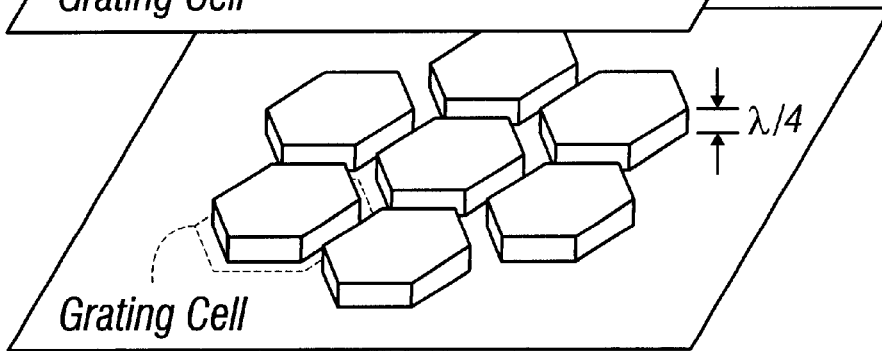


FIG. 4B

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MULTI-DIRECTIONAL RADIATION COUPLING IN QUANTUM-WELL INFRARED PHOTODETECTORS

CROSS REFERENCE TO RELATED APPLICATIONS

Continuity Statement This application claims the benefit of U.S. Provisional Application No. 60/141,185, filed on Jun. 25, 1999.

FEDERAL RESEARCH STATEMENT

The devices and techniques described herein were made in the performance of work under a NASA contract, and are subject to the provisions of Public Law 96-517 (35 U.S.C. §202) in which the Contractor has elected to retain title.

BACKGROUND OF INVENTION

This application relates to quantum-well radiation detectors, and more specifically, to radiation coupling to quantum-well photodetectors.

Quantum-well structures can be used to construct photodetectors to detect radiation with a high sensitivity. One type of quantum-well photodetectors use light absorption by transitions between different quantum energy states within the same band, either the conduction or the valance band of their quantum-well structures. Such transitions within the same band are also referred to as intersubband transitions.

Quantum physics dictates that an intersubband transition is excited to absorb photons of input radiation only when the electric field of the photons (i.e., the polarization) has a component along the growth direction of a quantum-well structure, i.e., perpendicular to the quantum layers. A coupling mechanism is often implemented in such quantum-well detectors to achieve the above-desired coupling condition. Random reflectors, corrugated surfaces, and grating couplers have been used to convert normally incident radiation to waves have components that propagate along the quantum well layers.

SUMMARY OF INVENTION

The present disclosure includes techniques for coupling radiation to a quantum-well detector based on intersubband transitions by using a special grating coupler. In one embodiment, this special grating includes a two-dimensional array of periodic grating cells. Each cell is shaped to define at least three different grating directions.

A central region and a peripheral region of different thickness values may be included in each cell to reduce the amount of energy in the zeroth diffraction order of the grating coupler. The peripheral region conforms to and surrounds the central region. The difference in optical thickness of the central and peripheral regions may be about one quarter of a selected radiation wavelength. In addition, the areas of the central and peripheral regions may be substantially the same.

This grating coupler may be formed directly over the quantum-well detector so that the array of the grating cells is substantially parallel to the quantum well layers of the detector. A conductive contact layer may be formed over the grating coupler is electrically biased relative to another contact layer formed on the other side of the quantum well layers.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 shows one embodiment of an integrated intersubband-transition quantum-well detector with a multi-

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directional grating coupler formed of a two-dimensional array of polygon grating cells.

FIG. 2 shows typical optical paths within the detector in FIG. 1 when an input beam is incident to the receiving side of the detector at the normal direction.

FIG. 3 shows hexagonal structure of the polygon grating cells of FIG. 1 according to one implementation.

FIGS. 4A and 4B illustrate two different configurations of the hexagonal structure shown in FIG. 3.

DETAILED DESCRIPTION

An optical grating includes a periodic structure to interact with light. The interference between diffracted light from the periodic structure produces a diffraction field in which the energy is distributed according to the Bragg phase matching conditions. Specifically, only certain diffraction directions that satisfy the Bragg phase matching conditions have constructive interference (i.e., bright spots) while all other directions have destructive interference (i.e., "dark spots"). The present radiation coupling is in part based on a two-dimensional periodic structure with a unique design to provide periodic perturbation to light in multi directions within a plane, i.e., more than three different directions. This can be used to couple radiation to an intersubband transition quantum-well detector with a high coupling efficiency.

FIG. 1 shows one embodiment of an intersubband-transition quantum-well detector **100** with a multi-directional grating coupler **120**. A semiconductor substrate is processed to form a quantum-well detector layer **101** with a single or an array of quantum-well detectors. The quantum-well detector layer **101** includes multiple quantum well layers of alternating barrier and active semiconductor layers that are perpendicular to their growth direction. Such a structure can be designed to support intersubband transitions, which are usually in the infrared spectral range.

On one side of the quantum well detector layer **101**, a transparent contact layer **110** is formed in parallel with the quantum well layers from a doped semiconductor material. The doping level in the contact layer **110** is sufficient to make it electrically conductive to provide a proper electrical bias to that side of the detector layer **101**. An antireflective layer for one wavelength or a spectral range of the radiation to be detected may be formed on the side of the contact layer **110** that is not in contact with the detector layer **101**. The index of refraction of the contact layer **110** is generally different from and is higher than that of the air. Hence, the interface between the contact layer **110** and the air is at least partly reflective due to this index difference. A beam reflected from the grating layer **120** can then be reflected at this interface back to the detector layer **101** to be further absorbed and hence to increase the detector efficiency. In operation, this side of the detector layer **101** is used as the receiving side to receive an input beam.

The grating coupler **120** is formed on the other side of the detector layer **101** opposite to the side with the contact layer **110**. A doped and conducting semiconductor contact layer is first formed in contact with this side of the detector layer **101**. Then the layer is patterned to form multiple identical grating cells, which are evenly spaced from one another to form a periodic two-dimensional grating cell array. Each grating cell has a polygon geometry with three or more pairs of opposing and parallel sides. The direction perpendicular to each pair of opposing and parallel sides defines one grating direction. Hence, the grating cell array has three or more grating directions.

This grating coupler **120** serves at least two different functions. One is a grating operation to diffract an input

beam along three or more different grating directions within the plane of the coupler **101**. This grating may be designed to operate in a reflection mode, i.e., the constructive diffraction orders are reflected back. Another function is to operate as a contact layer, similar to the contact layer **110**, to provide a proper electrical bias to the detector layer **101**. The electrical potentials applied to the layers **110** and **120** are different from each other to create a voltage drop across the quantum well detector layer **101** and hence to activate it.

The detector **100** may also include a reflective layer **130** to ensure that an input beam transmitted through the detector layer **101** is reflected back. This increases the detection efficiency. In addition, this reflective layer **130** may be made of a metallic layer, as illustrated in FIG. 1, by using a metalization process so that it can be used as an ohmic contact. Electrical contact nodes **140A** and **140B**, which may be made of Indium, can be formed in ohmic contact with the conducting reflective layer **130** and the conducting transparent contact layer **110**, respectively. A detector circuit **150** may be coupled to the nodes **140A** and **140B**.

FIG. 2 illustrates the typical operation of the detector **100** when an input beam **210** is incident approximately at the normal direction to the quantum well layers in the detector layer **101**. The beam **210** enters the detector layer **101** by transmitting through the contact layer **110** on the receiving side. Because the direction of the beam **210** is approximately parallel to the growth direction of the quantum well layers, the polarization of the beam **210** is approximately perpendicular to the growth direction (i.e., parallel to the layers). Hence, the intersubband absorption is small or about zero. The beam **210**, essentially unabsorbed, reaches and interacts with the grating coupler **120** to become reflected diffraction beam **220**. Only one diffraction beam **220** is shown but there are at least two other reflected diffraction beams since the grating layer **120** has at least three grating directions. The grating coupler **120** is designed so that the diffraction beam **220** is not the zeroth order diffraction but instead one or more higher order diffractions. The diffraction beam **220** hence is not parallel to the input beam **210**. When the diffraction beam **220** reaches the interface between the contact layer **110** and the air on the receiving side, it is reflected back to the detector layer **101** as a beam **230** because of the index difference at the interface. The beam **230** is not parallel to the input beam **210** and hence can be continuously absorbed by the detector layer **101**. The thickness H of the detector layer **101** can be purposefully made much smaller than its width W so that the diffraction beam **220** can be reflected multiple times within the detector layer **101** before it reaches the side boundary to increase the light absorption and thus the detection efficiency. For example, in one implementation, the width W of each detector region in the detector layer **101** may be about 30 microns and the thickness H of the layer **101** may be only about 3 microns.

FIG. 3 shows one embodiment **300** of the grating coupler **120** of FIG. 1, where each grating cell, e.g., **301** and **302**, is a hexagon with six sides **312A**, **313A**, **314A**, **312B**, **313B**, and **314B**. All hexagon grating cells are in the same orientation and are arranged in a periodic pattern. Any two adjacent cells are separated by a constant spacing D . This grating coupler **200** has three grating directions $G1$, $G2$, and $G3$, each angularly rotated by an equal amount of 120 degrees from another. The opposing and parallel pair of sides **212A** and **212B** define a first grating direction $G1$, the pair of sides **213A** and **213B** define a second grating direction $G2$, and the pair of sides **214A** and **214B** define a third grating direction $G3$. The grating period for each grating direction is the spacing D between the cells.

Referring to the grating cell **302**, each grating cell has a central region **310** and a peripheral region **320**. The peripheral region **320** surrounds the central region **310** and conforms to the boundary of the central region **310**. The regions **310** and **320** of each cell are configured to have different characteristics so that the optical interaction spatially varies from the region **310** to the region **320** in each cell. This spatial variation may be the phase delay of each reflected light ray. For example, regions **310** and **320** may have different thickness values so that a light ray reflected from region **310** has a different phase delay than a reflected light ray from the region. The regions **310** and **320** may also have different indices of refraction so the phase delays upon reflection in the regions **310** and **320** are different.

In addition, the regions **310** and **320** may be designed so that the difference in the phase delay upon reflection for a normal incident ray at the different regions **310** and **320** is approximately 180 degrees. This condition can reduce or minimize the amount of energy in the zeroth order diffraction (the geometrical reflection beam) and hence increase the diffraction energy in one or more selected high-order diffractions. Under this condition, the difference in the optical thickness (i.e., the index multiplied by the physical thickness) of the regions **310** and **320** should be one quarter of one wavelength of the radiation to be detected.

Furthermore, the areas of the regions **310** and **320** may be set so that the total reflected power from the central region **310** is approximately equal to the total reflected power from the peripheral region **320** from each cell. This effect, in a combination with the above difference in the phase delay of about 180 degrees, can be used to essentially eliminate the zeroth order diffraction by the grating coupler **120**. In general, the regions **310** and **320** may have different areas when their indices of refraction are different. In an implementation where regions **310** and **320** have the same index of refraction, their areas can be set equal.

FIGS. 4A and 4B show two configurations of the hexagonal design shown in FIG. 3. In FIG. 4A, the thickness of the central region **310** is less than that of the thickness of the peripheral region **320**. FIG. 4B shows the opposite situation.

Assuming the grating layer **120** extends infinitely, the angles of the m -th order diffraction can be written as

$$\sin(\Theta_m) = m\lambda/D - \sin(\Theta), \quad (m = \dots, -2, -1, 0, 1, 2, 3, \dots)$$

where Θ_m is the m -th order diffraction angle, Θ is the incident angle, λ is the wavelength of the input beam within the grating layer **120**, and D is the grating period for along each grating direction. The angles Θ_m and Θ are measured from the normal direction of the detector layer **101**. Hence, the polarization component along the growth direction of the quantum-well layers is proportional to $\cos(\Theta_m)$. Therefore, it may be desirable to set the value of the grating period D so that, for a given input wavelength λ , the diffraction angle Θ_m is as large as being practically possible and the zero-th order diffraction (reflection) is substantially suppressed. The coupling efficiency for along each grating direction is $\cos^2(\Theta_m)$.

The grating layer **120** may be further designed so each grating direction produces two diffraction orders. For example, the grating cells may be designed to diffract all energy into the ± 1 diffraction orders for each grating direction. Referring back to FIG. 2, the input beam **210** is shown to be diffracted into diffraction beams **220** and **240**. Since there are at least 3 grating directions, 6 or more reflected diffraction beams are produced. This can significantly increase the detection efficiency.

The above polygon design of each grating cell allows the two-dimensional grating coupler **120** to diffract an input beam along three or more different directions. Hence, the grating coupler **120** can diffract more light at higher diffraction orders than a grating coupler with only one or two grating directions. However, there may be a trade-off between the effective diffracting area and the number of grating directions in the grating coupler **120**. Octagonal grating cells or other more complex grating cells may be used to increase the number of the grating directions. However, these and other cell geometries have “dead” spaces between adjacent cells. The hexagonal design with six equal polygon sides can be used to achieve a fill factor of 100%, which may be better than other cell designs.

The exemplary detector **100** shown in FIGS. **1** and **2** uses an integrated structure without a substrate. This structure may be fabricated by the following process. First, a semiconductor substrate is prepared and the doped contact layer **110** is formed over the substrate by using, for example, the molecular beam epitaxy. Then, the multiple quantum well layers are formed over the contact layer **110** to form the detector layer **101**. Next, the contact layer **120** is formed and patterned to have the array of polygon grating cells. This may be achieved by first using the photolithography or electron beam lithography to print the pattern of the polygon pattern array on the contact layer **120** and then etching the exposed layer **120** by, e.g., chemical or reactive ion etching, to form the polygon pattern array. Subsequently, the top reflective layer **130** is formed. The above process completes fabrication of all layers in the detector **100**. Then underlying substrate is removed to form the detector **100**.

Alternatively, the substrate may be retained. The contact layer **110** may be positioned between the quantum well detector layer **101** and the substrate where the substrate is used to receive and transmit the input radiation to the detector layer **101**. The contact layer **110** may also be positioned so that the detector layer **101** is direction formed over one side of the substrate and the contact layer **110** is formed on an opposite side of the substrate. In this case, the substrate is doped so the electrical potential on the contact layer **110** can be applied to the detector layer **101**.

The materials for various structures in the above designs may be selected according to the requirements for the applications. For example, the receiving contact layer **101** may be GaAs or InP with a thickness about 0.4 micron. The quantum well detector layer **101** may typically include about 50 period of alternatively-grown quantum well layers and barrier layers of a total thickness in a range about 2.5–3.0 microns. The quantum well structure may use a combination of GaAs, AlGaAs, InAlAs, InGaAs, InGaAsP, or InP. The grating coupler **120** may use GaAs of about 0.2 micron in its thickness. The grating depth, i.e., the difference between the regions **310** and **320** of a cell may be about 0.8 micron. The top metal reflector may be formed of a metal such as gold, about 0.05 micron thick. The dimension of each quantum well detector along the quantum well layers is set to include multiple grating cells. For example, this dimension may be about 30 microns.

A number of embodiments of the invention have been described. Nevertheless, it will be understood that various modifications and enhancements may be made without departing from the following claims.

What is claimed is:

1. A device, comprising:

a detector layer having multiple quantum-well layers and responsive to radiation with a polarization component substantially parallel to said quantum-well layers; and

a grating layer formed over said detector layer to have a two-dimensional array of grating unit cells and to diffract an input beam into at least one diffraction direction not perpendicular to said quantum-well layers, each unit cell shaped to define at least three different grating directions within said grating layer, wherein each unit cell includes a central region and a peripheral region conforming to and surrounding said central region,

wherein central region and said peripheral region have different characteristics to effectuate a phase difference between a light ray reflected from said peripheral region and another light ray reflected from said central region.

2. The device as in claim **1**, wherein said central and said peripheral regions have different thicknesses.

3. The device as in claim **2**, wherein said central region and said peripheral region have a thickness difference substantially equal to one quarter of one wavelength of said input beam.

4. The device as in claim **2**, wherein said central and said peripheral regions of each cell are configured to reflect about the same amount of optical power.

5. The device as in claim **2**, wherein said central region has an area substantially equal to an area of said peripheral region.

6. The device as in claim **1**, wherein each unit cell is shaped as a hexagon to have three pairs of parallel and opposing sides which are perpendicular to said three grating directions, respectively.

7. The device as in claim **1**, wherein each unit cell is a polygon with an even number of sides greater than six.

8. The device as in claim **1**, further comprising:

a reflective layer directly formed over said grating layer; and

a transparent layer formed on one side of said detector layer opposing an opposite side that has said grating layer.

9. The device as in claim **8**, wherein both of said reflective layer and said transparent layer are electrically conductive to couple an electric bias to said detector layer.

10. A device, comprising:

at least one quantum-well detector formed of quantum-well layers; and

a grating layer formed over a first side of said detector to have a two-dimensional array of grating cells to diffract an input beam into a least one diffraction direction not perpendicular to said quantum-well layers, each cell being a polygon with at least three pairs of parallel and opposing sides to define at least three different grating directions.

11. The device as in claim **10**, wherein each grating cell is a polygon with at least six sides and includes a central region and a peripheral region conforming to and surrounding said central region, wherein central region and said peripheral region have different characteristics to effectuate a phase difference of about 180 degrees between a light ray reflected from said peripheral region and another light ray reflected from said region.

12. The device as in claim **10**, wherein said detector has a dimension along said quantum-well layers greater than a total thickness of said quantum well layers so that a reflected beam along said diffraction direction is reflected by both sides of said quantum well layers said detector at least once to transverse said quantum well layers at least twice.

13. The device as in claim **10**, wherein said grating layer is formed of a doped semiconductor to provide an electrical potential to said detector.

14. The device as in claim 13, further comprising a transparent contact layer on a side of said quantum well layers opposing said layer, wherein said contact layer is formed of a doped semiconductor.

15. The device as in claim 10, wherein each grating cell is a hexagon cell with equal six sides.

16. A device, comprising a grating layer having a two-dimensional array of grating cells, each cell being a polygon with at least three pairs of parallel and opposing sides to define at least three different grating directions, wherein each grating cell includes a central region and a peripheral region conforming to and surrounding said central region, which have a difference in their optical thickness values about one quarter of a selected radiation wavelength.

17. The device as in claim 16, wherein said central region has an index of refraction different from an index of refraction of said peripheral region.

18. The device as in claim 16, wherein said central and said peripheral regions of each cell are configured to reflect about the same amount of optical power.

19. A method, comprising:

preparing a substrate;

forming a first contact layer over said substrate;

forming a detector layer over said first contact layer to include a plurality of quantum-well layers;

forming a second contact layer over said detector layer;

patterning said second contact layer to form a periodic array of polygon cells to define at least three grating directions, each cell having a central region and a peripheral region with different characteristics to cause different phase delays in reflecting input light rays; and removing said substrate from a structure which includes said first contact layer, said detector layer, and said patterned second contact layer.

20. The device as in claim 1, wherein said multiple quantum-well layers include GaAs.

21. The device as in claim 10, wherein said multiple quantum-well layers include GaAs.

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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,423,980 B1
DATED : July 23, 2002
INVENTOR(S) : Sumith V. Bandara et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [75], please correct the inventor order as follows:

-- [75] Inventors: **Sumith V. Bandara**; **Sarath D. Gunapala**, both of Stevenson Ranch; **Daniel W. Wilson** of Glendale; **John K. Liu** of Pasadena, all of CA (US) --

Signed and Sealed this

Tenth Day of June, 2003

A handwritten signature in black ink, appearing to read "James E. Rogan", written over a horizontal line.

JAMES E. ROGAN
Director of the United States Patent and Trademark Office